

### INCHANGE SEMICONDUCTOR

### isc N-Channel Mosfet Transistor

## BUZ76

- FEATURES
- Drain Source Voltage-
  - : V<sub>DSS</sub>= 400V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)}$  = 1.8  $\Omega$  (Max)
- Fast Switching Speed
- Low Drive Requirement
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRITION

Designed for witched mode power supplies,motor control, welding,DC-DC & DC-AC converters, and in general purpose switching applications.switching regulators, switching converters.

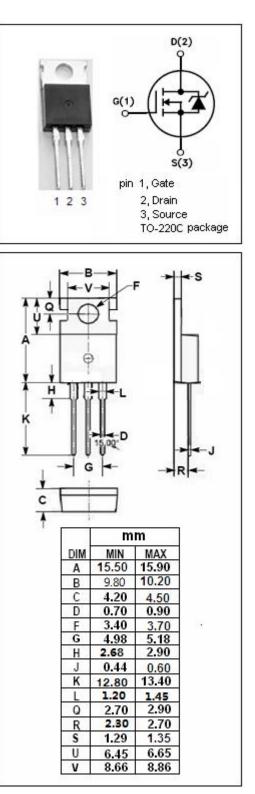
SYMBOL	ARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	400	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
ID	Drain Current-continuous@ TC=37℃	3	А
I <sub>DM</sub>	Drain Current-Single Plused	12	А
P <sub>tot</sub>	Total Dissipation@TC=25°C	40	W
Tj	Max. Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3.1	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	75	°C/W

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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =0.25mA	400			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.1		4.0	V
$V_{\text{SD}}$	Diode Forward On-voltage	I <sub>S</sub> = 6A ;V <sub>GS</sub> = 0			1.4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 2A			1.8	Ω
lgss	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =400V; V <sub>GS</sub> = 0			1	μA
Gfs	Forward Transconductance	V <sub>DS</sub> = 25V; I <sub>D</sub> =2A	2.1			S
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =10V;			12	
tr	Rise Time	I <sub>D</sub> =2.5A;			45	
$t_{d(off)}$	Turn-off Delay Time	V <sub>DD</sub> =30V; R <sub>GS</sub> =50 Ω			75	ns
t <sub>f</sub>	Fall Time				40	

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